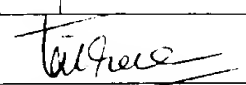


FORM PTO-1449 (REV. 7-80)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. NIT-304		SERIAL NO.	
<b>LIST OF DOCUMENTS CITED BY APPLICANT</b> <i>(Use several sheets if necessary)</i>				APPLICANT T. OSABE et al		GROUP	
				FILING DATE September 4, 2001			
<b>U.S. PATENT DOCUMENTS</b>							
* EXAMINER INITIAL		DOCUMENT	DATE	NAME	CLASS	SUBCLASS	FILING DATE <i>(If Appropriate)</i>
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
<b>FOREIGN PATENT DOCUMENTS</b>							
		DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
	AL						<input type="checkbox"/> <input type="checkbox"/>
	AM						<input type="checkbox"/> <input type="checkbox"/>
	AN						<input type="checkbox"/> <input type="checkbox"/>
	AO						<input type="checkbox"/> <input type="checkbox"/>
	AP						<input type="checkbox"/> <input type="checkbox"/>
<b>OTHER DOCUMENTS</b> <i>(Including Author, Title, Date, Pertinent Pages, etc.)</i>							
TT	AR	Kume et al, "Flash Memory Technology", Ouyou Butsuri, Vol. 65, p. 1114, 1996.					
TT	AS	J.D.Bude et al, "EEPROM/Flash Sub 3.0V Drain-Source Bias Hot Carrier Writing", IEEE International Electron Device Meeting 1995, p. 989-991.					
TT	AT	Ogura et al, "Low Voltage, Low Current, High Speed Program Step Split Gate Cell with Ballistic Direct Injection for EEPROM/Flash", IEEE International Electron Device Meeting, 1998, pp. 987-990.					
EXAMINER				DATE CONSIDERED			
				08/02			
<small>* EXAMINER: Initial if reference is considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>							

PC997 U.S. PTO  
 09/944073  
 09/04/01

FORM PTO-1449 (REV. 7-80)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. NIT-304	SERIAL NO.
<b>LIST OF DOCUMENTS CITED BY APPLICANT</b> <i>(Use several sheets if necessary)</i>		APPLICANT T. OSABE et al	
		FILING DATE September 4, 2001	GROUP

**U.S. PATENT DOCUMENTS**

* EXAMINER INITIAL	DOCUMENT	DATE	NAME	CLASS	SUBCLASS	FILING DATE (If Appropriate)
	AA					
	AB					
	AC					
	AD					
	AE					
	AF					
	AG					
	AH					
	AI					
	AJ					
	AK					

**FOREIGN PATENT DOCUMENTS**

DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
					YES	NO
AL					<input type="checkbox"/>	<input type="checkbox"/>
AM					<input type="checkbox"/>	<input type="checkbox"/>
AN					<input type="checkbox"/>	<input type="checkbox"/>
AO					<input type="checkbox"/>	<input type="checkbox"/>
AP					<input type="checkbox"/>	<input type="checkbox"/>

**OTHER DOCUMENTS** *(Including Author, Title, Date, Pertinent Pages, etc.)*

TT	AR	T. Jung et al, "A.3.3V 128Mb Multi-Level NAND Flash Memory for Mass Storage Application", IEEE International Solid-State Circuit Conference 1996, pp. 32-33, 1996.
+T	AS	M. Lorenzini et al, "A Dual Gate Flash EEPROM Cell with Two-Bit Storage Capacity", IEEE Transactions on Components, Packaging, and Manufacturing Technology Part A, Vol. 20, No. 2, p. 182, 1997.
+T	AT	

EXAMINER 	DATE CONSIDERED 08/02
--------------	--------------------------

\* EXAMINER Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.